TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7WZ00FU,TC7WZ00FK

#### **Dual 2 Input NAND Gate**

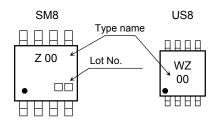
#### **Features**

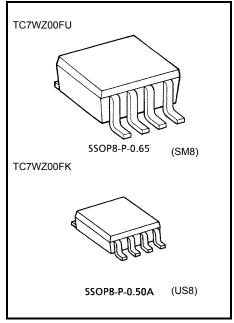
- High output drive: ±24 mA (min) at V<sub>CC</sub> = 3 V
- Super high speed operation: t<sub>pd</sub> = 2.4 ns (typ.)

at  $V_{CC} = 5 \text{ V}, 50 \text{ pF}$ 

- Operation voltage range: V<sub>CC (opr)</sub> = 1.65~5.5 V
- 5.5-V tolerant inputs
- 5.5-V power down protection outputs
- Matches the performance of TC74LCX series when operated at 3.3-V V<sub>CC</sub>

#### Marking





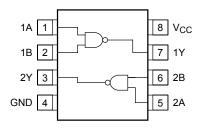
Weight

SSOP8-P-0.65 : 0.02 g (typ.) SSOP8-P-0.50A : 0.01 g (typ.)

#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Power supply voltage	Vcc	-0.5~6	V
DC input voltage	V <sub>IN</sub>	-0.5~6	٧
DC output voltage	Vout	-0.5~6	٧
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	-20	mA
DC output current	lout	±50	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	P <sub>D</sub> 300 (SM8) 200 (US8)		mW
Storage temperature	T <sub>stg</sub>	-65~150	°C
Lead temperature (10s)	TL	260	°C

### Pin Assignment (top view)





#### **Truth Table**

Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

# **Logic Diagram**



# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	Voc	1.65~5.5	V	
Supply voltage	Vcc	1.5~5.5 (Note 1)		
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~5.5 (Note 2)	V	
		0~V <sub>CC</sub> (Note 3)		
Operating temperature	T <sub>opr</sub>	-40~85	°C	
	d <sub>t</sub> /d <sub>v</sub>	$0 \sim 20 \; (V_{CC} = 1.8 \; V \pm 0.15 \; V, \\ 2.5 \; V \pm 0.2 \; V)$	ns/V	
Input rise and fall time		$0 \sim 10 \; (V_{CC} = 3.3 \; V \pm 0.3 \; V)$		
		0~5 (V <sub>CC</sub> = 5.5 V ± 0.5 V)		

Note 1: Data retention only

Note 2:  $V_{CC} = 0 V$ 

Note 3: High or low state



### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol	Tost	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit
Cilarac	densucs	Syllibol	rest Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Onit
	High level	n level V <sub>IH</sub>	_		1.65~ 1.95	0.75 × V <sub>CC</sub>	_	_	0.75 × V <sub>CC</sub>		V
Input	riigirievei				2.3~5.5	0.7 × V <sub>CC</sub>	_	_	0.7 × V <sub>CC</sub>	_	
voltage	Low level		_		1.65~ 1.95		_	0.25 × V <sub>CC</sub>	ı	0.25 × V <sub>CC</sub>	
	Low level	V <sub>IL</sub>			2.3~5.5		_	0.3 × V <sub>CC</sub>		0.3 × V <sub>CC</sub>	
					1.65	1.55	1.65	_	1.55	_	
				$I_{OH} = -100 \mu A$	2.3	2.2	2.3	_	2.2	_	
				ΙΟΗ – 100 μ/	3.0	2.9	3.0	_	2.9	_	
					4.5	4.4	4.5	_	4.4	_	
	High level	Voн	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52	_	1.29	_	V
				$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.15	_	1.9	_	
				$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.8	_	2.4	_	
				$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.68	_	2.3	_	
Output				$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.2	_	3.8	_	
voltage	Low level	VoL	V <sub>IN</sub> = V <sub>IH</sub>	Ι <sub>ΟL</sub> = 100 μΑ	1.65	_	0	0.1	_	0.1	
					2.3	_	0	0.1	_	0.1	
					3.0	_	0	0.1	_	0.1	
					4.5	_	0	0.1	_	0.1	
				I <sub>OL</sub> = 4 mA	1.65	_	80.0	0.24	_	0.24	
				$I_{OL} = 8 \text{ mA}$	2.3	_	0.1	0.3	_	0.3	
				I <sub>OL</sub> = 16 mA	3.0	_	0.15	0.4	_	0.4	
				I <sub>OL</sub> = 24 mA	3.0	_	0.22	0.55	_	0.55	
				$I_{OL} = 32 \text{ mA}$	4.5	_	0.22	0.55	_	0.55	
Input leakage current $I_{IN}$ $V_{IN} = 5.5 \text{ V or GND}$		or GND	0~5.5	_	_	±1	_	±10	μΑ		
Power off leakage current I <sub>0</sub>		l <sub>OFF</sub>	V <sub>IN</sub> or V <sub>OUT</sub> = 5.5 V		0.0	_	_	1	_	10	μΑ
Quiescent su	pply current	Icc	$V_{IN} = 5.5 V$	or GND	1.65~5.5	_	_	1	—	10	μΑ

### AC Characteristics (unless otherwise specified, Input: $t_r = t_f = 3$ ns)

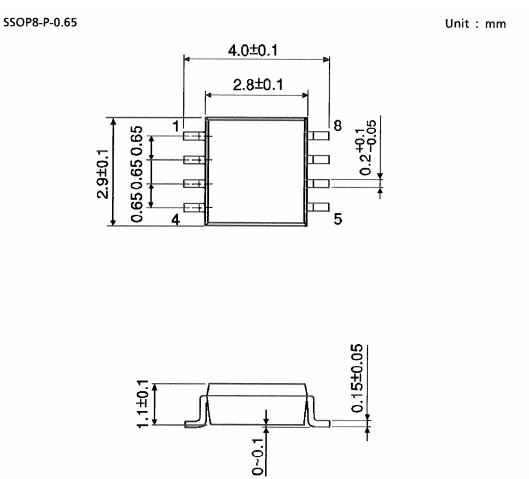
Characteristics	Cumbal	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
Propagation delay time	<sup>t</sup> pLH <sup>t</sup> pHL	$C_L$ = 15 pF, $R_L$ = 1 M $\Omega$	1.8 ± 0.15	2.0	5.3	9.6	2.0	9.8	- ns
			2.5 ± 0.2	1.2	3.2	5.3	1.2	5.7	
			3.3 ± 0.3	0.8	2.4	3.7	0.8	4.0	
			5.0 ± 0.5	0.5	1.9	2.9	0.5	3.2	
		$C_L = 50$ pF, $R_L = 500 \Omega$	$3.3 \pm 0.3$	1.2	3.0	4.6	1.2	4.9	
			5.0 ± 0.5	0.8	2.4	3.6	0.8	3.9	
Input capacitance	CIN	_	0~5.5	_	3.0	_	_	_	pF
Power dissipation capacitance	C <sub>PD</sub>	(Note 4)	3.3		22		_	_	- pF
		(Note 4)	5.5		32		_		

Note 4: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

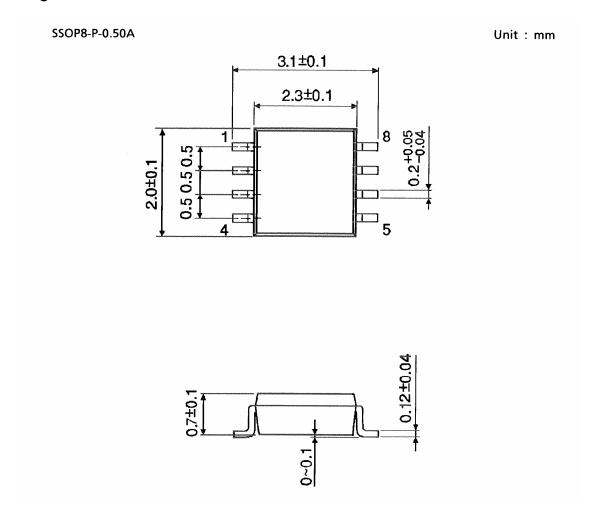
 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$ 

### **Package Dimensions**



Weight: 0.02 g (typ.)

### **Package Dimensions**



Weight: 0.01 g (typ.)

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